

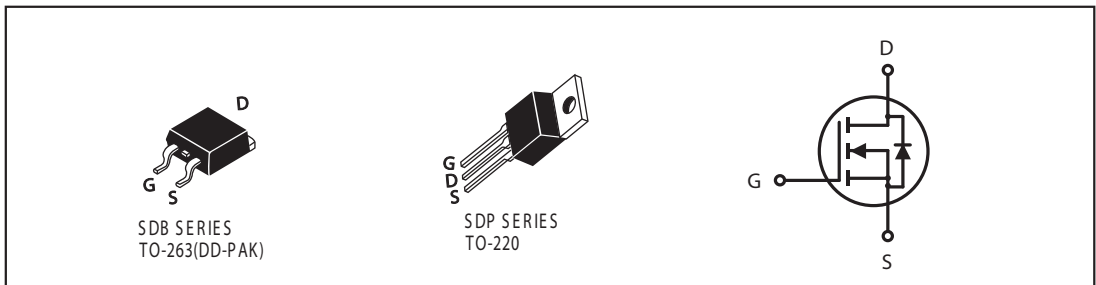


N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DS}	I _D	R _{DS(on)} (mΩ) Max
20V	32A	19 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- TO-220 & TO-263 package.



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous @ T _J =125°C -Pulsed ^a	I _D	23	A
	I _{DM}	57	A
Drain-Source Diode Forward Current	I _S	55	A
Maximum Power Dissipation @ T _c =25°C	P _D	75	W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to 175	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R _{θJC}	2	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	°C/W

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ELECTRICAL CHARACTERISTICS (T_c = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250µA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16V, V _{GS} = 0V			10	µA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±8V, V _{DS} = 0V			±100	nA
ON CHARACTERISTICS^a						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250µA	0.9	1	1.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 21A		14	19	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	40			A
Forward Transconductance	g _{FS}	V _{DS} = 10V, I _D = 26A		53		S
DYNAMIC CHARACTERISTICS^b						
Input Capacitance	C _{ISS}	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz		1100		pF
Output Capacitance	C _{OSS}			600		pF
Reverse Transfer Capacitance	C _{RSS}			180		pF
SWITCHING CHARACTERISTICS^b						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 10V, I _D = 1A, V _{GS} = 10V R _{GEN} = 6 ohm		50		ns
Rise Time	t _r			62.5		ns
Turn-Off Delay Time	t _{D(OFF)}			200		ns
Fall Time	t _f			89		ns
Total Gate Charge	Q _g	V _{DS} = 10V, I _D = 30A, V _{GS} = 4.5V		18.2		nC
Gate-Source Charge	Q _{gs}			5.3		nC
Gate-Drain Charge	Q _{gd}			2.2		nC

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ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^a						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{V}, I_s = 26\text{A}$		0.9	1.3	V

Notes

- a. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

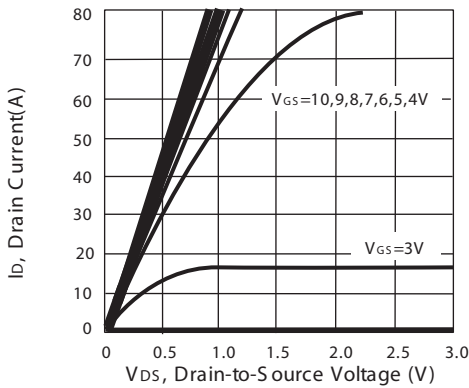


Figure 1. Output Characteristics

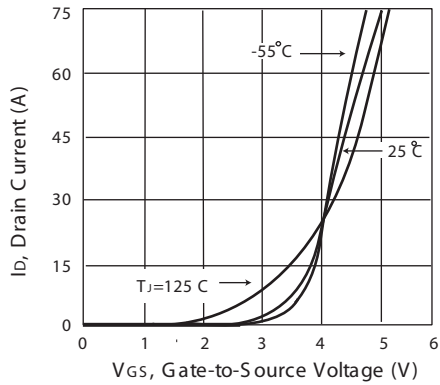


Figure 2. Transfer Characteristics

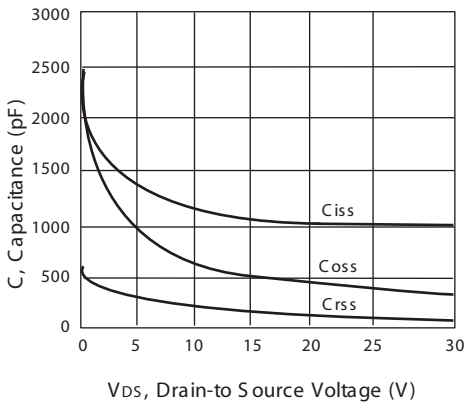


Figure 3. Capacitance

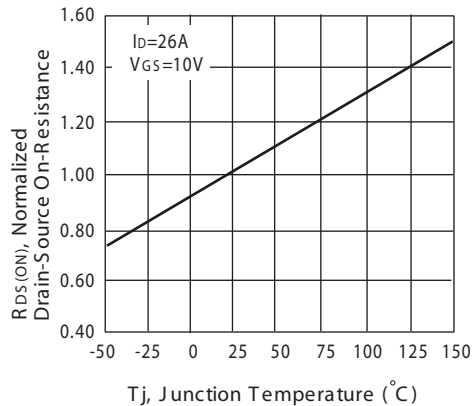


Figure 4. On-Resistance Variation with Temperature

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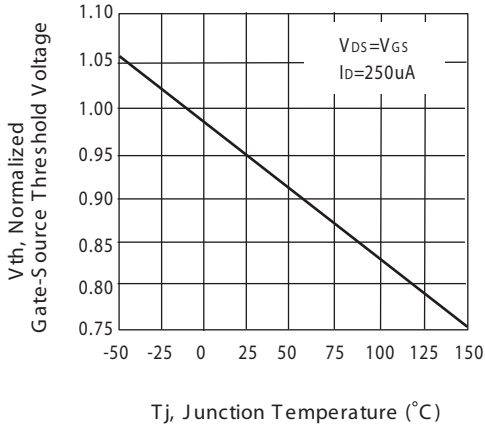


Figure 5. Gate Threshold Variation with Temperature

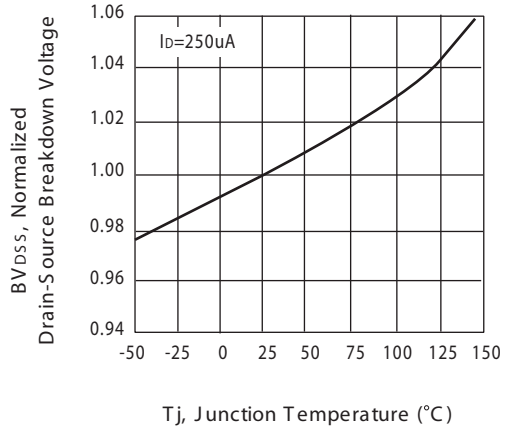


Figure 6. Breakdown Voltage Variation with Temperature

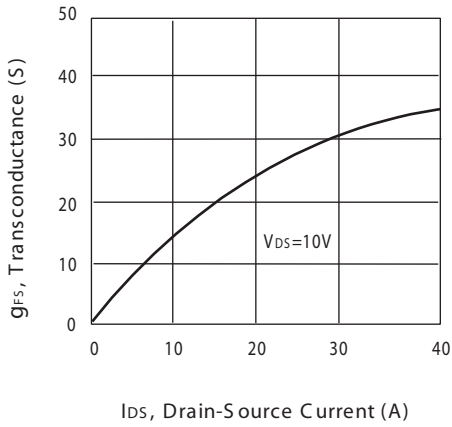


Figure 7. Transconductance Variation with Drain Current

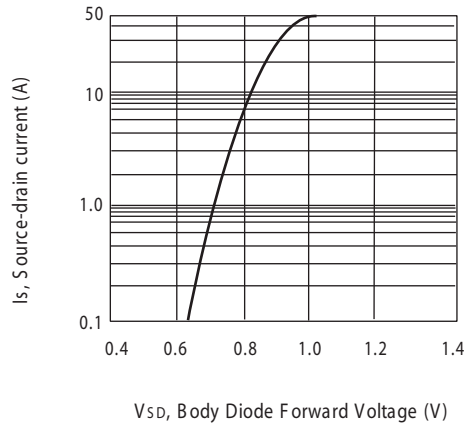


Figure 8. Body Diode Forward Voltage Variation with Source Current

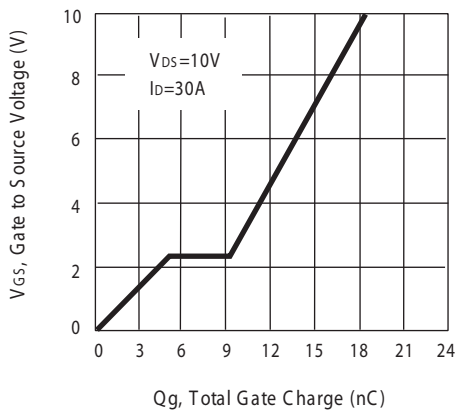


Figure 9. Gate Charge

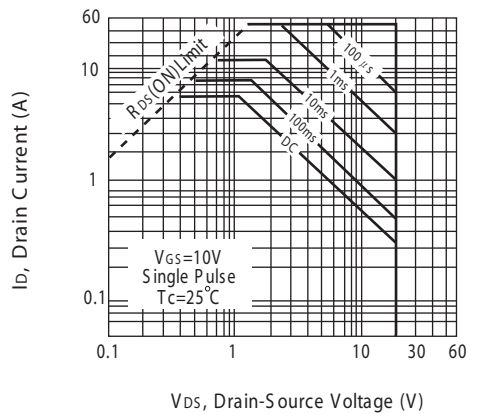


Figure 10. Maximum Safe Operating Area

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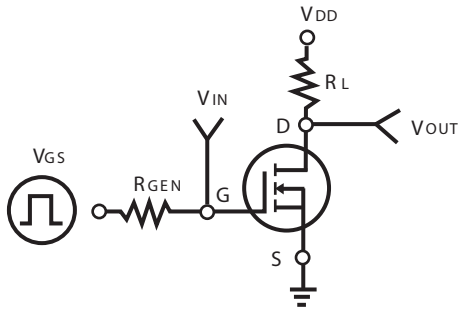


Figure 11. Switching Test Circuit

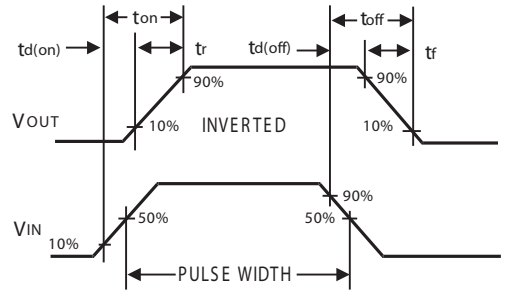


Figure 12. Switching Waveforms

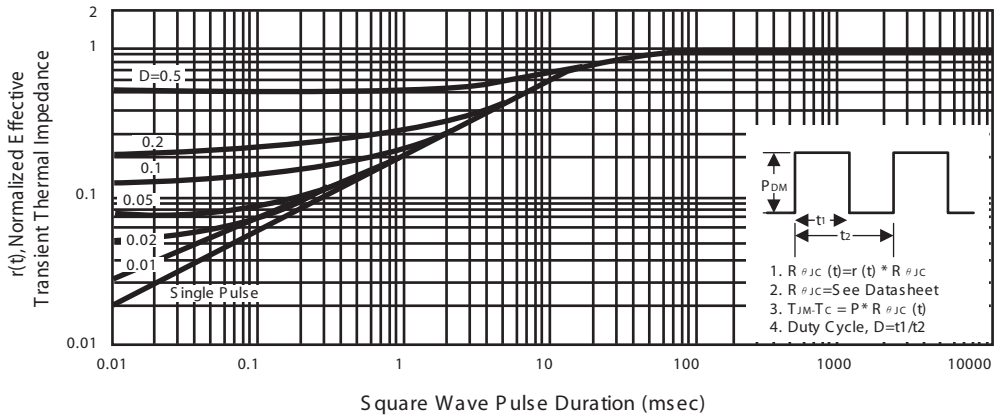
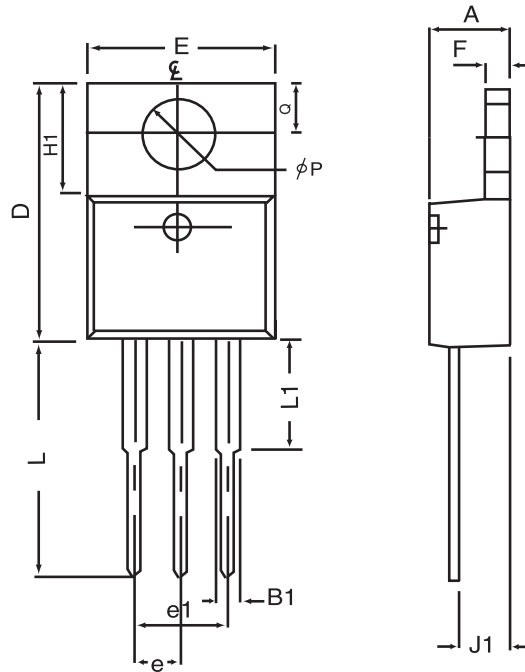


Figure 13. Normalized Thermal Transient Impedance Curve

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PACKAGE OUTLINE DIMENSIONS

TO-220



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.32	4.80	0.170	0.189
B1	1.27	1.65	0.050	0.630
D	14.6	16.00	0.575	0.610
E	9.70	10.41	0.382	0.410
e	2.34	2.74	0.092	0.108
e1	4.68	5.48	0.184	0.216
F	1.14	1.40	0.045	0.055
H1	5.97	6.73	0.235	0.265
J1	2.20	2.79	0.087	0.110
L	12.88	14.22	0.507	0.560
L1	3.00	6.35	0.120	0.250
ϕP	3.50	3.94	0.138	0.155
Q	2.54	3.05	0.100	0.120